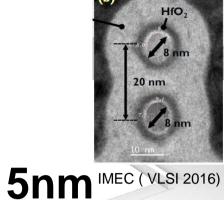
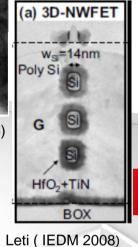


SCALING ROADMAP

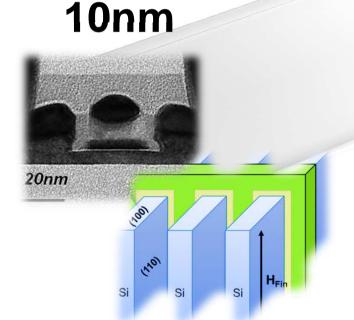






leti

7_{nm}





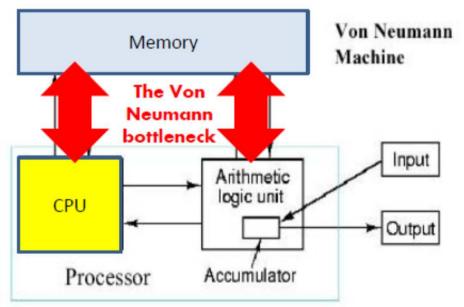
S. Barraud et al, session 17.6 Vertically Stacked-NanoWires MOSFETs in a Replacement Metal Gate Process with Inner Spacer and SiGe Source/Drain



VON NEUMANN PROCESSOR

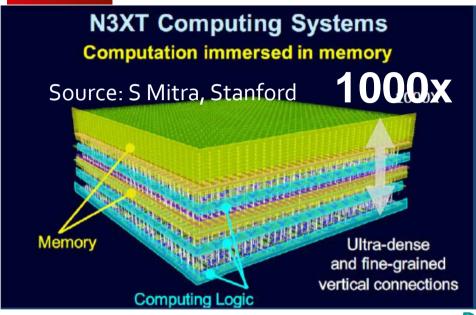
A Von Neumann processor can execute an arbitrary sequence of instructions on arbitrary data but the instructions and data must flow over a **limited capacity bus** connecting the processor and main memory.

Thus, the processor cannot execute a program faster than it can fetch instructions and data from memory.



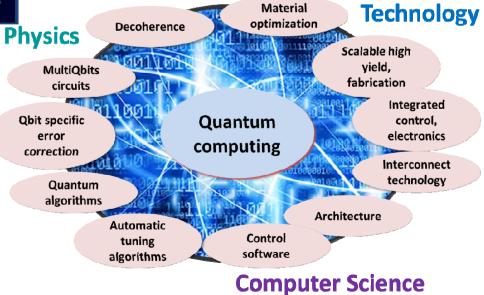


NEW COMPUTING PARADIGMS



Massive parallelism Quantum computing

Computation Immersed in Memory



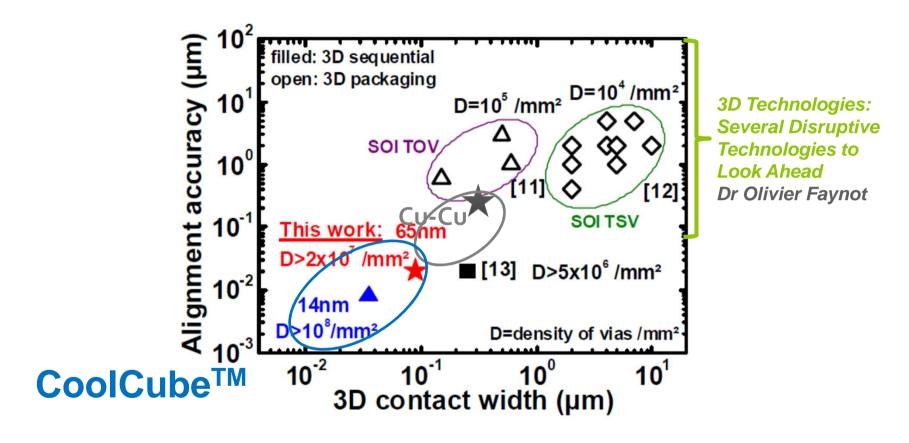


WHICH DEVICES FOR NEW COMPUTING PARADIGMS?

Leti Devices Workshop | Maud Vinet | December 4th, 2016

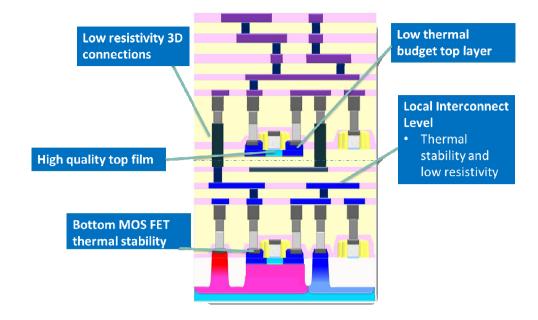


HIGH DENSITY 3D TECHNOLOGIES



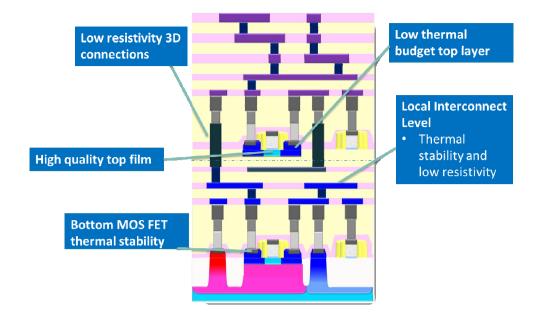
Above 2x10⁷vias/mm² demonstrated with CoolCube[™] Reachable 3D via pitch @ 14nm = 80nm





- Top Junction Performance?
- Inter Metal Interconnects?
- Is It a Manufacturable Process?
- 4. Do You Really Benefit From the Lithographic Alignment?





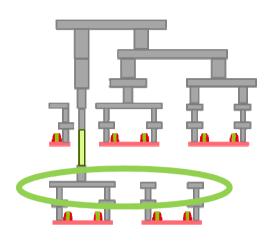
- Top Junction Performance?
 Same as bottom one (Pasini, VLSI 2015 and 2016)
- 2. Inter Metal Interconnects?

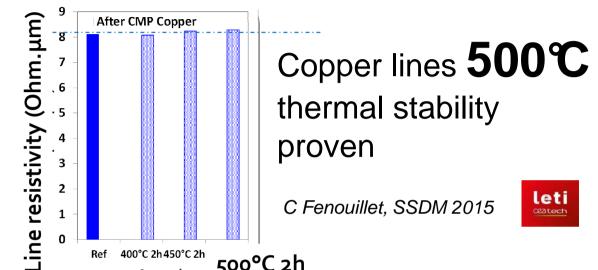


- Is It a Manufacturable Process?
- 4. Do You Really Benefit from The Lithographic Alignment?



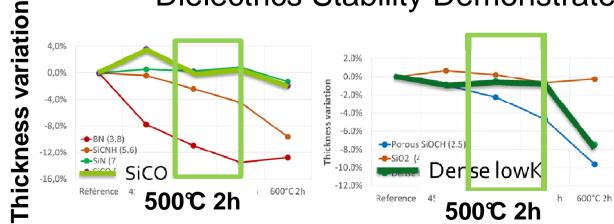
WHAT ABOUT INTER LAYERS INTERCONNECTS?





Dielectrics Stability Demonstrated

500°C 2h



400°C 2h 450°C 2h

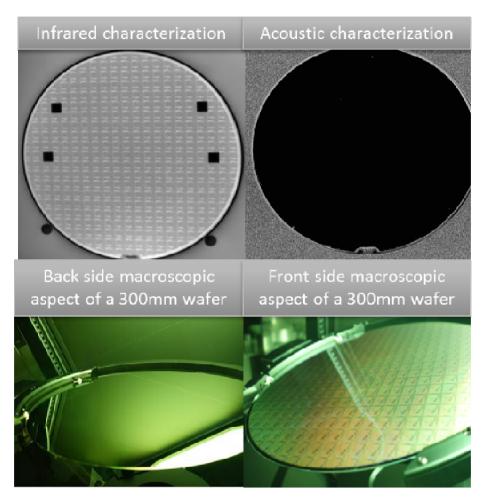
Anneals

F Deprat, MAM 2016





300mm WAFERS IN PRODUCTION FAB

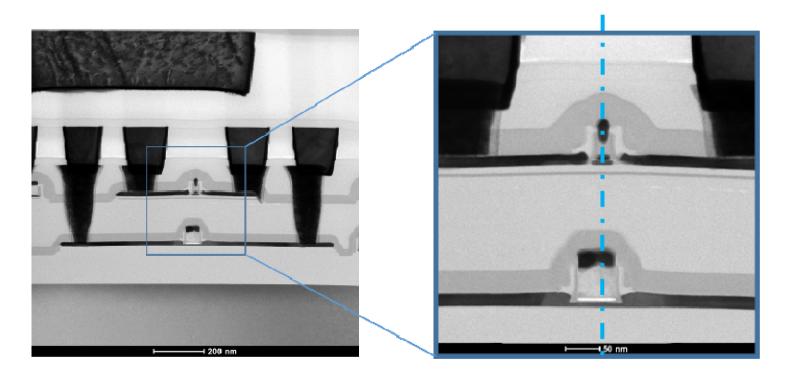


No macroscopic bonding defects at 300mm wafer scale





NANOMETRIC LITHOGRAPHY ALIGNMENT AT **WAFER SCALE**

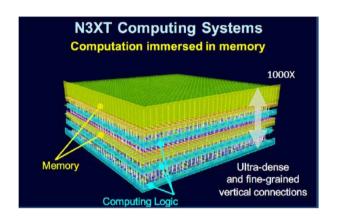


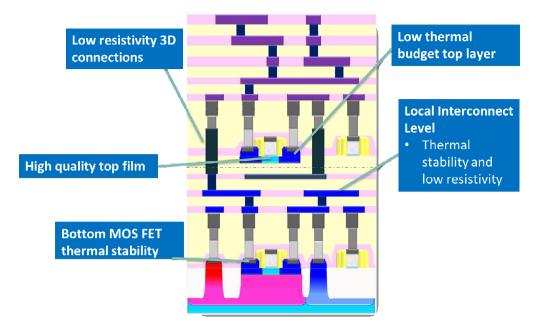
No Impact of Layer Deformation During Bonding and Thinning





CoolCubeTM



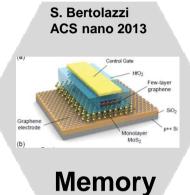


- **Top Junction Performance**
- Inter Metal Interconnects
- Manufacturable Process
- Lithographic Alignment



2D TMD (TRANSITION METAL DICHALCOGENIDES)

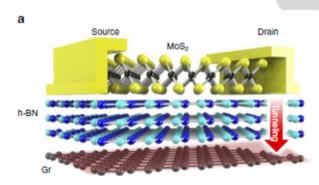
Opportunities for Logic and Non-Volatile Memory Co-Integration



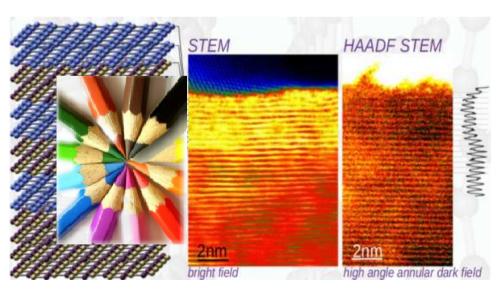
Spintronics

Spin Logic with Ferromagnetic **Memories**

Geim et al, Manchester team: 'Graphene cake'

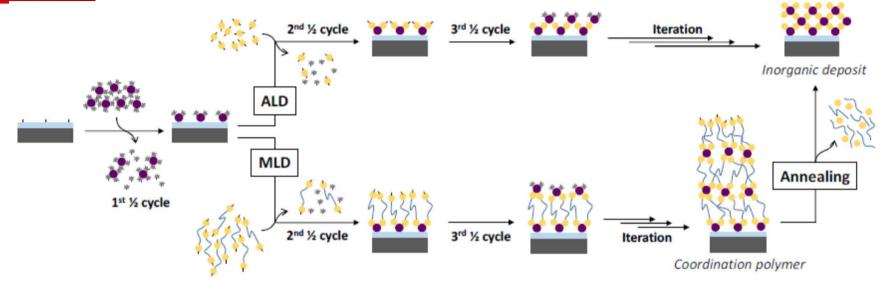


Quoc An Vu, Nature Comm, 2016

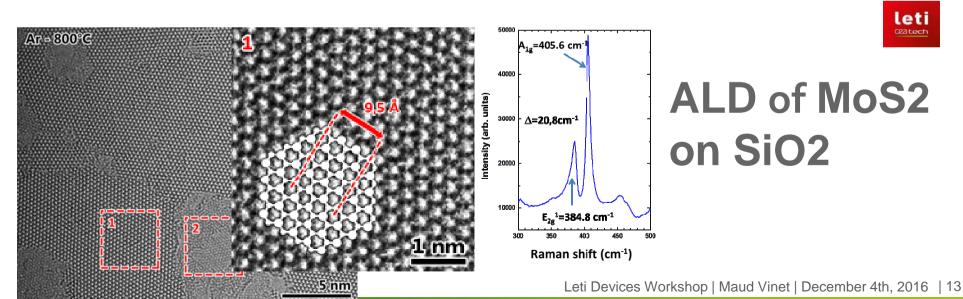




2D TMD LARGE SCALE GROWTH



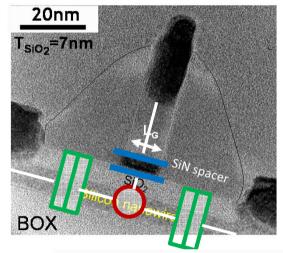
Low-temperature Atomic Layer Deposition of MoS2 using a novel organometallic precursor S. Cadot, et al, ALD 2015



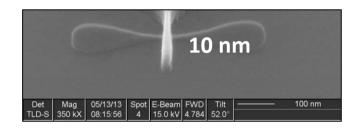


NANOWIRES TO DESIGN QUANTUM DOTS

Quantum Electronic for Efficient Computing Dr Silvano de Franceschi

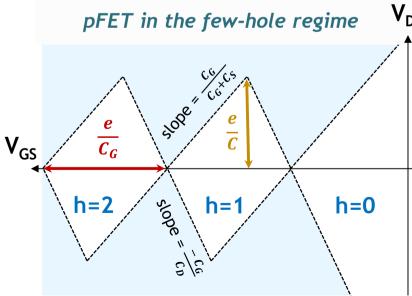


Wide Spacers over thin, undoped SOI



V. Deshpande, IEDM 2012, M. Vinet IEDM 2013

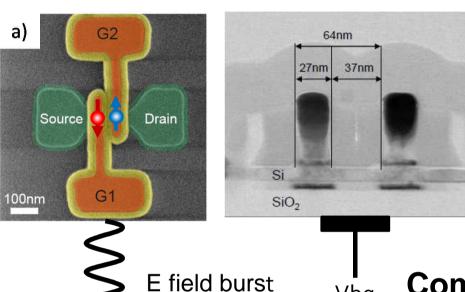




FETs are Turned into Single Electron or Single Hole Transistor



SI SPIN QUBITS EXTEND NANOWIRES OPERATION



Definition of a Two-Level System with Long Quantum Coherence

Communication Via Tunable Quantum Coupling Between Qubits

Control of A Single Qubit: Initialization, Manipulation

L. Hutin et al., VLSI Tech. Symp. 2016

R. Maurand et al., Nature Comm 2016

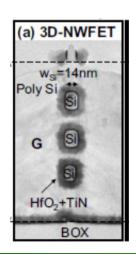
5. De Franceschi et al, 13.4 SOI Technology for Quantum Information Processing (Invited)



Vbg





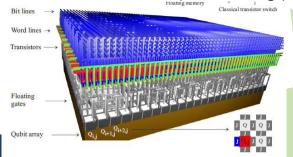


Leti advanced technologies of today

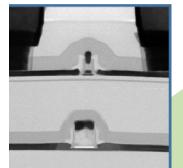


ROADMAP

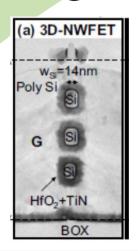
M. Veldhorst et al., https://arxiv.org/pdf/1609.09700.pdf

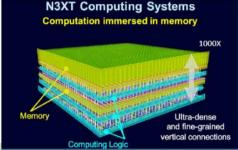


2025



2016





2020 Logic in memory

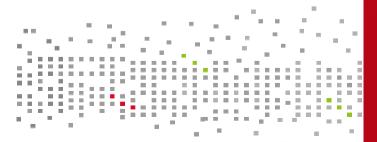


Quantum Computing

Neuromorphic computing

Leti advanced technologies of today are supporting the shift in computing paradigms

Thank you for your attention



Leti, technology research institute

Commissariat à l'énergie atomique et aux énergies alternatives Minatec Campus | 17 rue des Martyrs | 38054 Grenoble Cedex | France www.leti.fr

